TOSHIBA Field Effect Transistor Silicon $N$ Channel MOS Type ( $\pi$-MOSVII)

## TK7P50D

## Switching Regulator Applications

- Low drain-source ON-resistance: $\mathrm{RDS}(\mathrm{ON})=1.0 \Omega$ (typ.)
- High forward transfer admittance: $\left|\mathrm{Y}_{\mathrm{fs}}\right|=2.5 \mathrm{~S}$ (typ.)
- Low leakage current: IDSS $=10 \mu \mathrm{~A}(\max )\left(\mathrm{V}_{\mathrm{DS}}=500 \mathrm{~V}\right)$
- Enhancement-mode: Vth $=2.4$ to $4.4 \mathrm{~V}(\mathrm{VDS}=10 \mathrm{~V}, \mathrm{ID}=1 \mathrm{~mA})$


## Absolute Maximum Ratings ( $\mathbf{T a}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Characteristics |  | Symbol | Rating | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Drain-source voltage |  | $V_{\text {DSS }}$ | 500 | V |
| Gate-source voltage |  | $V_{G S S}$ | $\pm 30$ | V |
| Drain current | DC (Note 1) | ID | 7 | A |
|  | Pulse ( $\mathrm{t}=1 \mathrm{~ms}$ ) <br> (Note 1) | IDP | 28 |  |
| Drain power dissipation ( $\mathrm{Tc}=25^{\circ} \mathrm{C}$ ) |  | PD | 100 | W |
| Single pulse avalanche energy <br> (Note 2) |  | $\mathrm{EAS}_{\text {AS }}$ | 105 | mJ |
| Avalanche current |  | $\mathrm{I}_{\text {AR }}$ | 7 | A |
| Repetitive avalanche energy (Note 3) |  | $\mathrm{EAR}_{\text {AR }}$ | 10 | mJ |
| Channel temperature |  | $\mathrm{T}_{\mathrm{ch}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature range |  | $\mathrm{T}_{\text {stg }}$ | -55 to 150 | ${ }^{\circ} \mathrm{C}$ |

Unit: mm


Weight : 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Thermal resistance, channel to case | $\mathrm{R}_{\text {th }}$ (ch-c) | 1.25 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal resistance, channel to ambient | $\mathrm{R}_{\text {th }}$ (ch-a) | 125 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Note 1: Please use devices on conditions that the channel temperature is below $150^{\circ} \mathrm{C}$.
Note 2: $\mathrm{V}_{\mathrm{DD}}=90 \mathrm{~V}, \mathrm{~T}_{\mathrm{ch}}=25^{\circ} \mathrm{C}$ (initial), $\mathrm{L}=3.64 \mathrm{mH}, \mathrm{R}_{\mathrm{G}}=25 \Omega, \mathrm{I}_{\mathrm{AR}}=7 \mathrm{~A}$
Note 3: Repetitive rating: pulse width limited by maximum channel temperature
This transistor is an electrostatic sensitive device. Please handle with caution.


Electrical Characteristics ( $\mathrm{Ta}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Characteristics |  | Symbol | Test Condition | Min | Typ. | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Gate leakage current |  | IGSS | $\mathrm{V}_{\mathrm{GS}}= \pm 30 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ | - | - | $\pm 1$ | $\mu \mathrm{A}$ |
| Drain cut-off current |  | IDSS | $\mathrm{V}_{\mathrm{DS}}=500 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$ | - | - | 10 | $\mu \mathrm{A}$ |
| Drain-source breakdown voltage |  | $V$ (BR) DSS | $\mathrm{I}_{\mathrm{D}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$ | 500 | - | - | V |
| Gate threshold voltage |  | $V_{\text {th }}$ | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=1 \mathrm{~mA}$ | 2.4 | - | 4.4 | V |
| Drain-source ON-resistance |  | $\mathrm{R}_{\mathrm{DS}}(\mathrm{ON})$ | $\mathrm{V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=3.5 \mathrm{~A}$ | - | 1.0 | 1.22 | $\Omega$ |
| Forward transfer admittance |  | $\left\|Y_{f s}\right\|$ | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=3.5 \mathrm{~A}$ | 0.7 | 2.5 | - | S |
| Input capacitance |  | Ciss | $\mathrm{V}_{\mathrm{DS}}=25 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | - | 600 | - | pF |
| Reverse transfer capacitance |  | Crss |  | - | 4 | - |  |
| Output capacitance |  | $\mathrm{C}_{\text {oss }}$ |  | - | 70 | - |  |
| Switching time | Rise time | $\mathrm{tr}_{r}$ | Duty $\leq 1 \%, \mathrm{t}_{\mathrm{w}}=10 \mu \mathrm{~s}$ | - | 18 | - | ns |
|  | Turn-on time | $t_{\text {on }}$ |  | - | 40 | - |  |
|  | Fall time | $t_{f}$ |  | - | 8 | - |  |
|  | Turn-off time | $\mathrm{t}_{\text {off }}$ |  | - | 55 | - |  |
| Total gate charge |  | $\mathrm{Q}_{\mathrm{g}}$ | $\mathrm{V}_{\mathrm{DD}} \approx 400 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=7 \mathrm{~A}$ | - | 12 | - | nC |
| Gate-source charge |  | $\mathrm{Q}_{\mathrm{gs}}$ |  | - | 7 | - |  |
| Gate-drain charge |  | $\mathrm{Q}_{\mathrm{gd}}$ |  | - | 5 | - |  |

Source-Drain Ratings and Characteristics ( $\mathrm{Ta}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ )

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Continuous drain reverse current <br> (Note 1) | IDR | - | - | - | 7 | A |
| Pulse drain reverse current (Note 1) | IDRP | - | - | - | 28 | A |
| Forward voltage (diode) | V ${ }_{\text {DSF }}$ | $\mathrm{I}_{\mathrm{DR}}=7 \mathrm{~A}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$ | - | - | -1.7 | V |
| Reverse recovery time | trr | $\begin{aligned} & \mathrm{I} \mathrm{DR}=7 \mathrm{~A}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}, \\ & \mathrm{dl}_{\mathrm{DR}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s} \end{aligned}$ | - | 1200 | - | ns |
| Reverse recovery charge | $Q_{\text {rr }}$ |  | - | 7 | - | $\mu \mathrm{C}$ |

## Marking (Note 4)



Note 4: * Weekly code: (Four digits)

Week of manufacture
(01 for first week of year, continuing up to 52 or 53)
Year of manufacture
(The last 2digits of the calendar year)












DYNAMIC INPUT / OUTPUT CHARACTERISTICS
 GATE-SOURCE VOLTAGE $\mathrm{V}_{\mathrm{GS}}(\mathrm{V})$



$$
\begin{aligned}
& \mathrm{R}_{\mathrm{G}}=25 \Omega \\
& \mathrm{~V}_{\mathrm{DD}}=90 \mathrm{~V}, \mathrm{~L}=3.64 \mathrm{mH}
\end{aligned} \quad \mathrm{EAS}=\frac{1}{2} \cdot \mathrm{~L} \cdot \mathrm{I}^{2} \cdot\left(\frac{\mathrm{BVDSS}}{\mathrm{BVDSS}^{-}-\mathrm{VDD}}\right)
$$

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